

PHYSICAL PROPERTIES
OF SENSOR STRUCTURES
ON THE BASIS OF SILICON $p-n$ JUNCTION
WITH INTERDIGITATED BACK CONTACTS

O. V. Kozynets', S. V. Litvinenko

Taras Shevchenko National University of Kyiv,
Institute of High Technologies of Kyiv
(2, blvd. 6, Prosp. Academician Glushkov,
Kyiv 01033, Ukraine; e-mail: alk@univ.kiev.ua)

S u m m a r y

The influence of the adsorption of water molecules on the photosensitivity of a silicon $p-n$ junction with interdigitated back contacts has been studied. It has been shown that the examined structures can be used for the creation of effective chemical sensors.